

# Paula Agopian

## List of Publications by Year in descending order

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papers

777  
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840776

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677142

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192  
docs citations

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times ranked

505  
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-Frequency Noise Analysis and Modeling in Vertical Tunnel FETs With Ge Source. IEEE Transactions on Electron Devices, 2016, 63, 1658-1665.	3.0	69
2	Temperature impact on the tunnel fet off-state current components. Solid-State Electronics, 2012, 78, 141-146.	1.4	68
3	Experimental Comparison Between Trigate p-TFET and p-FinFET Analog Performance as a Function of Temperature. IEEE Transactions on Electron Devices, 2013, 60, 2493-2497.	3.0	60
4	InGaAs tunnel FET with sub-nanometer $\langle i \rangle$ EOT $\langle /i \rangle$ and sub-60 $\hat{a}$ €%mV/dec sub-threshold swing at room temperature. Applied Physics Letters, 2016, 109, .	3.3	48
5	Influence of the Source Composition on the Analog Performance Parameters of Vertical Nanowire-TFETs. IEEE Transactions on Electron Devices, 2015, 62, 16-22.	3.0	29
6	Study of line-TFET analog performance comparing with other TFET and MOSFET architectures. Solid-State Electronics, 2017, 128, 43-47.	1.4	29
7	Threshold voltage extraction in Tunnel FETs. Solid-State Electronics, 2014, 93, 49-55.	1.4	28
8	Analog Figures of Merit of Vertically Stacked Silicon Nanosheets nMOSFETs With Two Different Metal Gates for the Sub-7 nm Technology Node Operating at High Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 3630-3635.	3.0	18
9	Analog performance of vertical nanowire TFETs as a function of temperature and transport mechanism. Solid-State Electronics, 2015, 112, 51-55.	1.4	17
10	Drain induced barrier thinning on TFETs with different source/drain engineering. , 2014, , .		14
11	Double Gate Tunnel-FET Working Like a Permittivity Based Biosensor with Different Drain to Gate and Drain to Biomaterial Alignments. ECS Journal of Solid State Science and Technology, 2019, 8, Q50-Q53.	1.8	13
12	Influence of 60-MeV Proton-Irradiation on Standard and Strained n- and p-Channel MuGFETs. IEEE Transactions on Nuclear Science, 2012, 59, 707-713.	2.0	11
13	NW-TFET analog performance for different Ge source compositions. , 2013, , .		11
14	Analog design with Line-TFET device experimental data: from device to circuit level. Semiconductor Science and Technology, 2020, 35, 055025.	2.0	11
15	Impact of the NW-TFET Diameter on the Efficiency and the Intrinsic Voltage Gain From a Conduction Regime Perspective. IEEE Transactions on Electron Devices, 2016, 63, 2930-2935.	3.0	10
16	Performance of TFET and FinFET devices applied to current mirrors for different dimensions and temperatures. Semiconductor Science and Technology, 2016, 31, 055001.	2.0	10
17	Study of the linear kink effect in PD SOI nMOSFETs. Microelectronics Journal, 2007, 38, 114-119.	2.0	9
18	Zero Temperature Coefficient behavior for advanced MOSFETs. , 2016, , .		9

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19	Intrinsic voltage gain of Line-TFETs and comparison with other TFET and MOSFET architectures. , 2016, , .		9
20	GR-Noise Characterization of Ge pFinFETs With STI First and STI Last Processes. IEEE Electron Device Letters, 2016, 37, 1092-1095.	3.9	9
21	Performance evaluation of Tunnel-FET basic amplifier circuits. , 2019, , .		9
22	Low frequency noise performance of horizontal, stacked and vertical silicon nanowire MOSFETs. Solid-State Electronics, 2021, 184, 108087.	1.4	9
23	Electron valence-band tunnelling excess noise in twin-gate silicon-on-insulator MOSFETs. Solid-State Electronics, 2006, 50, 52-57.	1.4	8
24	Fin shape influence on the analog performance of standard and strained MuGFETs. , 2010, , .		8
25	Back gate bias influence on SOI $\hat{\text{C}}$ -gate nanowire down to 10 nm width. , 2016, , .		8
26	Low-Frequency Noise Assessment of Different Ge pFinFET STI Processes. IEEE Transactions on Electron Devices, 2016, 63, 4031-4037.	3.0	8
27	Operational transconductance amplifier designed with nanowire tunnel-FET with Si, SiGe and Ge sources using experimental data. Semiconductor Science and Technology, 2020, 35, 095020.	2.0	8
28	Comparative analysis of the intrinsic voltage gain and unit gain frequency between SOI and bulk FinFETs up to high temperatures. Solid-State Electronics, 2016, 123, 124-129.	1.4	7
29	Impact of Biosensor Permittivity on a Double-Gate nTFET Ambipolar Current. ECS Transactions, 2018, 85, 187-192.	0.5	7
30	Analysis of current mirror circuits designed with line tunnel FET devices at different temperatures. Semiconductor Science and Technology, 2017, 32, 055015.	2.0	6
31	Impact of the twin-gate structure on the linear kink effect in PD SOI nMOSFETs. Microelectronics Journal, 2006, 37, 681-685.	2.0	5
32	Field effect transistors: From mosfet to Tunnel-Fet analog performance perspective. , 2014, , .		5
33	Fin width influence on analog performance of SOI and bulk FINFETs. , 2014, , .		5
34	Analysis of analog parameters in NW-TFETs with Si and SiGe source composition at high temperatures. , 2015, , .		5
35	Analog parameters of solid source Zn diffusion In <sub>x</sub> Ga <sub>1-x</sub> As nTFETs down to 10 K. Semiconductor Science and Technology, 2016, 31, 124001.	2.0	5
36	Performance of differential pair circuits designed with line tunnel FET devices at different temperatures. Semiconductor Science and Technology, 2018, 33, 075012.	2.0	5

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37	Cryogenic operation of graded-channel silicon-on-insulator nMOSFETs for high performance analog applications. <i>Microelectronics Journal</i> , 2006, 37, 137-144.	2.0	4
38	Transconductance ramp effect in high-k triple gate sSOI nFinFETs. , 2009, , .		4
39	Temperature Influence on Tunnel Field Effect Transistors (TFETs) with Low Ambipolar Currents. <i>ECS Transactions</i> , 2011, 39, 77-84.	0.5	4
40	Performance comparison between TFET and FinFET differential pair. , 2015, , .		4
41	Comparison between vertical silicon NW-TFET and NW-MOSFET from analog point of view. , 2015, , .		4
42	Effective hole mobility and low-frequency noise characterization of Ge pFinFETs. , 2016, , .		4
43	Experimental analysis of differential pairs designed with line tunnel FET devices. , 2017, , .		4
44	A Tunnel-FET device model based on Verilog-A applied to circuit simulation. , 2018, , .		4
45	Silicon Nanowire Tunnel-FET Differential Amplifier Using Verilog-A Lookup Table Approach. , 2019, , .		4
46	Gate dielectric material influence on DC behavior of MO(I)SHEMT devices operating up to 150°C. <i>Solid-State Electronics</i> , 2021, 185, 108091.	1.4	4
47	Impact of proton irradiation on strained triple gate SOI p- and n-MOSFETs. , 2011, , .		3
48	Experimental analog performance of pTFETs as a function of temperature. , 2012, , .		3
49	Comparative study of self-heating effects influence on triple-gate FinFETs fabricated on bulk, SOI and modified substrates. , 2013, , .		3
50	Temperature Influence on Strained nMuGFETs after Proton Radiation. <i>ECS Transactions</i> , 2013, 53, 171-176.	0.5	3
51	Experimental Comparison between pTFET and pFinFET under Analog Operation. <i>ECS Transactions</i> , 2013, 53, 155-160.	0.5	3
52	Unity gain frequency on FinFET and TFET devices. , 2014, , .		3
53	Proton Radiation Effects on the Analog Performance of Bulk n- and p-FinFETs. <i>ECS Transactions</i> , 2015, 66, 295-301.	0.5	3
54	Impact of the diameter of vertical nanowire-tunnel FETs with Si and SiGe source composition on analog parameters. , 2015, , .		3

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55	Different stress techniques and their efficiency on triple-gate SOI n-MOSFETs. Solid-State Electronics, 2015, 103, 209-215.	1.4	3
56	Low Temperature Effect on Strained and Relaxed Ge pFinFETs STI Last Processes. ECS Transactions, 2016, 75, 213-218.	0.5	3
57	The Influence of Oxide Thickness and Indium Amount on the Analog Parameters of In <sub>0.15</sub> Ga <sub>0.85</sub> As nTFETs. IEEE Transactions on Electron Devices, 2017, 64, 3595-3600.	3.0	3
58	Proton radiation effects on the self-aligned triple gate SOI p-type tunnel FET output characteristic. , 2017, , .		3
59	Intrinsic Voltage Gain of Stacked GAA Nanosheet MOSFETs Operating at High Temperatures. ECS Transactions, 2020, 97, 65-69.	0.5	3
60	Temperature influence on the gate-induced floating body effect parameters in fully depleted SOI nMOSFETs. Solid-State Electronics, 2008, 52, 1751-1754.	1.4	2
61	Halo Optimization for 0.13um SOI CMOS Technology. ECS Transactions, 2008, 14, 111-118.	0.5	2
62	DIBL performance of 60 MeV proton-irradiated SOI MuGFETs. , 2010, , .		2
63	Temperature impact on double gate nTFET ambipolar behavior. , 2011, , .		2
64	Impact of SEG on uniaxially strained MuGFET performance. Solid-State Electronics, 2011, 59, 13-17.	1.4	2
65	Uniaxial stress efficiency for different fin dimensions of triple-gate SOI nMOSFETs. , 2011, , .		2
66	A Compact Model and an Extraction Method for the FinFET Spreading Resistance. ECS Transactions, 2011, 39, 255-262.	0.5	2
67	Biaxial Stress Simulation and Electrical Characterization of Triple-Gate SOI nMOSFETs. ECS Transactions, 2012, 49, 145-152.	0.5	2
68	Fin width influence on uniaxial stress of triple-gate SOI nMOSFETs. , 2012, , .		2
69	Stress engineering and proton radiation influence on off-state leakage current in triple-gate SOI devices. Solid-State Electronics, 2013, 90, 155-159.	1.4	2
70	Back bias influence on analog performance of pTFET. , 2013, , .		2
71	Influence of X-ray radiation on standard and uniaxial strained triple-gate SOI FinFETs. , 2013, , .		2
72	Radiation effect on standard and strained triple-gate SOI FinFETs parasitic conduction. , 2013, , .		2

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73	Analog performance of standard and uniaxial strained triple-gate SOI FinFETs under x-ray radiation. Semiconductor Science and Technology, 2014, 29, 125015.	2.0	2
74	Vertical Nanowire TFET Diameter Influence on Intrinsic Voltage Gain for Different Inversion Conditions. ECS Transactions, 2015, 66, 187-192.	0.5	2
75	Comparison of Current Mirrors Designed with TFET or FinFET Devices for Different Dimensions and Temperatures. ECS Transactions, 2015, 66, 303-308.	0.5	2
76	Study of low frequency noise in vertical NW-Tunnel FETs with different source compositions. , 2015, , .		2
77	The smaller the noisier? Low frequency noise diagnostics of advanced semiconductor devices. , 2015, , .		2
78	(Invited) Generation-Recombination Noise in Advanced CMOS Devices. ECS Transactions, 2016, 75, 111-120.	0.5	2
79	Impact of the low temperature operation on long channel strained Ge pFinFETs fabricated with STI first and last processes. , 2016, , .		2
80	Split CV mobility at low temperature operation of Ge pFinFETs fabricated with STI first and last processes. Semiconductor Science and Technology, 2016, 31, 114002.	2.0	2
81	Comparative study of vertical GAA TFETs and GAA MOSFETs in function of the inversion coefficient. , 2016, , .		2
82	Influence of the Ge amount at source on transistor efficiency of vertical gate all around TFET for different conduction regimes. , 2016, , .		2
83	Analysis of proton irradiated n- and p-type strained FinFETs at low temperatures down to 100 K. Semiconductor Science and Technology, 2018, 33, 065003.	2.0	2
84	DC method for self-heating estimation applied to FinFET. , 2018, , .		2
85	Interface Charges Influence on the Subthreshold Region from Triple Gate SOI FinFET to $\hat{\alpha}$ , $\hat{\beta}$ -Gate Nanowire Devices. , 2018, , .		2
86	Opposite trends between digital and analog performance for different TFET technologies. , 2018, , .		2
87	Comparison between proton irradiated triple gate SOI TFETS and finfets from a TID point of view. Semiconductor Science and Technology, 2019, 34, 065003.	2.0	2
88	Output conductance at saturation like region on Line-TFET for different dimensions. , 2019, , .		2
89	Intrinsic Voltage Gain and Unit-Gain Frequency of Omega-Gate Nanowire SOI MOSFETs. , 2019, , .		2
90	Rebound effect on Charged Based Bio-TFETs for different biomolecules. , 2019, , .		2

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91	Study of a Fringing Field Biosensor Tunnel-FET. ECS Journal of Solid State Science and Technology, 2021, 10, 017004.	1.8	2
92	Impact of gate current on the operational transconductance amplifier designed with nanowire TFETs. Solid-State Electronics, 2021, 186, 108099.	1.4	2
93	OTA Performance Comparison Designed with Experimental NW-MOSFET and NW-TFET Devices. , 2019, , .		2
94	Analog Performance of Dynamic Threshold Voltage SOI MOSFET.. ECS Transactions, 2008, 14, 169-175.	0.5	1
95	Cross-Section Features Influence on Surrounding MuGFETs. ECS Transactions, 2010, 31, 91-98.	0.5	1
96	Radiation hardness aspects of advanced FinFET and UTBOX devices. , 2012, , .		1
97	Biaxial &#x002B; uniaxial stress effectiveness in tri-gate SOI nMOSFETs with variable fin dimensions. , 2012, , .		1
98	(Invited) The Impact of a (Si)Ge Heterojunction on the Analog Performance of Vertical Tunnel FETs. ECS Transactions, 2014, 64, 127-133.	0.5	1
99	Comparison of analog performance between SOI and Bulk pFinFET. , 2014, , .		1
100	The effect of X-Ray radiation dose rate on Triple-Gate SOI FinFETs parameters. , 2014, , .		1
101	The Impact of the Ge Concentration in the Source for Vertical Tunnel-FETs. ECS Transactions, 2015, 66, 79-86.	0.5	1
102	High temperature influence on analog parameters of Bulk and SOI nFinFETs. , 2015, , .		1
103	Impact of Gate Stack Dielectric on Intrinsic Voltage Gain and Low Frequency Noise in Ge pMOSFETs. ECS Transactions, 2015, 66, 309-314.	0.5	1
104	Impact of diameter on TFET conduction mechanisms. , 2015, , .		1
105	Influence of proton radiation and strain on nFinFET zero temperature coefficient. , 2016, , .		1
106	Analysis of TFET and FinFET differential pairs with active load from 300K to 450K. , 2016, , .		1
107	Low frequency noise and fin width study of silicon passivated germanium pFinFETs. , 2016, , .		1
108	Proton radiation influence on SOI FinFET trade-off between transistor efficiency and unit gain frequency. , 2016, , .		1

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109	Low-frequency and random telegraph noise performance of Ge-based and III-V devices on a Si platform. , 2016, , .		1
110	Experimental comparison between relaxed and strained Ge pFinFETs. , 2017, , .		1
111	Back gate influence on transistor efficiency of SOI nMOS $\hat{\text{C}}$ -gate nanowire down to 10nm width. , 2017, , .		1
112	Enhanced model for ZTC in irradiated and strained pFinFET. , 2017, , .		1
113	New method for observing self-heating effect using transistor efficiency signature. , 2017, , .		1
114	Impact of process and device dimensions on Bio-TFET Sensitivity. , 2018, , .		1
115	Influence of Channel Silicon Thickness and Biological Material Permittivity on nTFET Biosensor. , 2018, , .		1
116	New method for self-heating estimation using only DC measurements. , 2018, , .		1
117	Parasitic Conduction on $\hat{\text{C}}$ -Gate Nanowires SOI nMOSFETs. ECS Transactions, 2018, 85, 103-109.	0.5	1
118	A Negative-Bias-Temperature-Instability Study on Omega-Gate Silicon Nanowire SOI pMOSFETs. , 2019, , .		1
119	Device-Based Threading Dislocation Assessment in Germanium Hetero-Epitaxy. , 2019, , .		1
120	Impact of Gate Dielectric Material on Basic Parameters of MO(I)SHEMT Devices. ECS Transactions, 2020, 97, 53-58.	0.5	1
121	Influence of the Biomaterial Thickness in a Dielectrically Charged Modulated Fringing Field Bio-Tunnel-FET Device. ECS Transactions, 2020, 97, 109-114.	0.5	1
122	Sparse matrices for transient simulations with computing memory reduction. Electric Power Systems Research, 2020, 183, 106266.	3.6	1
123	Voltage gain improvement of the operational transconductance amplifier designed with silicon-on-insulator fin field effect transistor after being exposed to proton-irradiation. Semiconductor Science and Technology, 2021, 36, 035001.	2.0	1
124	Evaluation of Dielectrically Modulated and Fringing Field Tunneling Field Effect Transistor Biosensors Devices. ECS Journal of Solid State Science and Technology, 2021, 10, 077001.	1.8	1
125	Current mirror designed with GAA nanosheet MOSFETs from room temperature to 200 $\hat{\text{A}}$ °C. Semiconductor Science and Technology, 2021, 36, 095019.	2.0	1
126	Analysis of zero-temperature coefficient behavior on vertically stacked double nanosheet nMOS devices. Microelectronics Journal, 2021, 117, 105277.	2.0	1



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127	Total ionizing dose influence on proton irradiated triple gate SOI Tunnel FETs. Journal of Integrated Circuits and Systems, 2018, 13, 1-7.	0.4	1
128	Output Conductance of Line-TFETs for Different Device Parameters and its Effect on Basic Analog Circuits. Journal of Integrated Circuits and Systems, 2020, 15, 1-7.	0.4	1
129	Influence of the Biomaterial Thickness in a Dielectrically Charged Modulated Fringing Field Bio-Tunnel-FET Device. ECS Meeting Abstracts, 2020, MA2020-01, 1376-1376.	0.0	1
130	Two-stage amplifier design based on experimental Line-Tunnel FET data. , 2019, , .		1
131	Temperature influence on analog figures-of-merit of nanosheet nMOSFET devices for sub-7nm technology node. , 2020, , .		1
132	Design of operational transconductance amplifier with Gate-All-Around Nanosheet MOSFET using experimental data from room temperature to 200°C. Solid-State Electronics, 2022, 189, 108238.	1.4	1
133	Comparison between Low-Dropout Voltage Regulators Designed with Line and Nanowire Tunnel Field Effect Transistors using Experimental Data. Solid-State Electronics, 2022, , 108328.	1.4	1
134	The Impact of the Gate Oxide Thickness Reduction on the Gate Induced Floating Body Effect in SOI nMOSFETs. ECS Transactions, 2007, 9, 305-311.	0.5	0
135	The C Shape Behavior of the Floating Body Effect in Function of Temperature in PD SOI nMOSFETs. ECS Transactions, 2007, 6, 107-111.	0.5	0
136	The "U" Shape Behavior of GIFBE in Function of Back Gate Bias in FinFETs. ECS Transactions, 2009, 19, 317-320.	0.5	0
137	Strain Effectiveness Dependence on Fin Dimensions and Shape for n-type Triple-Gate MuGFETs. ECS Transactions, 2011, 39, 207-214.	0.5	0
138	Global and/or Local Strain Influence on p- and n MuGFET Analog Performance. ECS Transactions, 2011, 35, 145-150.	0.5	0
139	A Simple Electron Mobility Model Considering the Impact of Silicon-Dielectric Interface Orientation for Surrounding Gate Devices. ECS Transactions, 2011, 39, 179-186.	0.5	0
140	Alpha Radiation Incidence Angle Influence on Planar FDSOI nMOSFET. ECS Transactions, 2011, 39, 85-92.	0.5	0
141	Temperature Influence on Nanowire Tunnel Field Effect Transistors. ECS Transactions, 2012, 49, 223-230.	0.5	0
142	Uniaxial and/or Biaxial Strain Influence on MuGFET Devices. Journal of the Electrochemical Society, 2012, 159, H570-H574.	2.9	0
143	Comparative Experimental Study between Tensile and Compressive Uniaxially Stressed nMuGFETs under X-ray Radiation Focusing on Analog Behavior. ECS Transactions, 2013, 53, 177-185.	0.5	0
144	Fin Dimension Influence on Mechanical Stressors in Triple-Gate SOI nMOSFETs. ECS Transactions, 2013, 53, 187-192.	0.5	0

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145	Radiation Influence on Biaxial+Uniaxial Strained Silicon MuGFETs. ECS Transactions, 2013, 50, 205-212.	0.5	0
146	Graphene for advanced devices applications. , 2014, , .		0
147	The effect of X-Ray radiation on DIBL for standard and strained triple-gate SOI MuGFETs. , 2014, , .		0
148	Early voltage and intrinsic voltage gain in vertical nanowire-TFETs as a function of temperature. , 2014, , .		0
149	Study of Hysteresis in Vertical Ge-Source Heterojunction Tunnel-FETs at Low Temperature. ECS Transactions, 2015, 66, 179-185.	0.5	0
150	Transconductance hump in vertical gate-all-around tunnel-FETs. , 2015, , .		0
151	Dynamic threshold voltage influence on Ge pMOSFET hysteresis. , 2015, , .		0
152	On the assessment of electrically active defects in high-mobility materials and devices. , 2016, , .		0
153	Impact of $\text{In}_x\text{Ga}_{1-x}$ composition and source Zn diffusion temperature on intrinsic voltage gain in InGaAs TFETs. , 2016, , .		0
154	Influence of spacer materials on underlapped and self-aligned UTBB SOI nMOSFET. , 2016, , .		0
155	Analysis of the transistor efficiency of gas phase Zn diffusion $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ nTFETs at different temperatures. , 2017, , .		0
156	Low temperature performance of proton irradiated strained SOI FinFET. , 2017, , .		0
157	Simple method for detection of the self-heating signature. , 2017, , .		0
158	Subthreshold region analysis for UTBOX and UTBB SOI nMOSFETs with different channel lengths and silicon thickness. , 2017, , .		0
159	The influence of low-energy proton irradiation on threshold voltage and transconductance of nanowire SOI n and p-channel transistors. , 2017, , .		0
160	Low temperature influence on long channel STI last process relaxed and strained Ge pFinFETs. , 2017, , .		0
161	Impact of the Zn diffusion process at the source side of $\text{In}_x\text{Ga}_{1-x}$ nTFETs on the analog parameters down to 10 K. , 2017, , .		0
162	New approach for removing the self-heating from MOSFET current using only DC characteristics. , 2018, , .		0

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163	Ground Plane Impact on the Threshold Voltage of Relaxed Ge pFinFETs. , 2018, , .		0
164	Improvement of gm/IDMethod for Detection of Self-Heating Effects. ECS Transactions, 2018, 85, 73-78.	0.5	0
165	Analysis of Omega-Gate Nanowire Devices from Parasitic Conduction to Ionizing Radiation Effects. ECS Journal of Solid State Science and Technology, 2019, 8, Q54-Q60.	1.8	0
166	Experimental analysis and improvement of the DC method for self-heating estimation. Solid-State Electronics, 2019, 159, 171-176.	1.4	0
167	Proposal of a p-type Back-Enhanced Tunnel Field Effect Transistor. , 2019, , .		0
168	Transmission Line Model Based on PCB Units and Modified ĩ€ Circuits. , 2019, , .		0
169	Impact of Drain Doping and Biomaterial Thickness in a Dielectrically Modulated Fringing Field Bio-TFET Device. , 2019, , .		0
170	Comparison between nMOS and pMOS Ĩ-gate nanowire down to 10 nm width as a function of back gate bias. Semiconductor Science and Technology, 2019, 34, 035003.	2.0	0
171	Proton-Irradiation Influence on Current Mirror Circuit Using Verilog-A Approach Based on Experimental SOI FinFET Characteristics. ECS Transactions, 2020, 97, 171-177.	0.5	0
172	Readout Circuit Design Using Experimental Data of Line-TFET Devices. ECS Transactions, 2020, 97, 165-170.	0.5	0
173	Study of Underlapped Finfets Behavior for a Radiation Sensing Purpose. ECS Transactions, 2020, 97, 121-126.	0.5	0
174	Analysis of the ZTC-Point for Vertically Stacked Nanosheet pMOS Devices. , 2021, , .		0
175	Impact of Positive Charges in a Fringing Field Bio-Tunnel-FET Device with Source Underlap. , 2021, , .		0
176	Simple Analytical Modelling of an Electronically Tunable Potentiometer and Body Factor Influence. , 2021, , .		0
177	The Impact of Spacer Oxide Material on the Underlapped SOI-nFinFET Working as Charged Based Radiation Sensor. Journal of Integrated Circuits and Systems, 2021, 16, 1-6.	0.4	0
178	Study of the UTBB BESOI Tunnel-FET working as a Dual-Technology Transistor. Journal of Integrated Circuits and Systems, 2021, 16, 1-6.	0.4	0
179	High Temperature Influence on the Trade-off between gm/I<sub>D</sub> and f<sub>T</sub> of nanosheet NMOS Transistors with Different Metal Gate Stack. , 2021, , .		0
180	Readout Circuit Design Using Experimental Data of Line-TFET Devices. ECS Meeting Abstracts, 2020, MA2020-01, 1390-1390.	0.0	0

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181	Proton-Irradiation Influence on Current Mirror Circuit Using Verilog-A Approach Based on Experimental SOI FinFET Characteristics. ECS Meeting Abstracts, 2020, MA2020-01, 1380-1380.	0.0	0
182	Intrinsic Voltage Gain of Stacked GAA Nanosheet MOSFETs Operating at High Temperatures. ECS Meeting Abstracts, 2020, MA2020-01, 1395-1395.	0.0	0
183	Study of Underlapped Finfets Behavior for a Radiation Sensing Purpose. ECS Meeting Abstracts, 2020, MA2020-01, 1379-1379.	0.0	0
184	Analysis of Omega-Gate Nanowire SOI MOSFET Under Analog Point of View. Journal of Integrated Circuits and Systems, 2020, 15, 1-6.	0.4	0
185	Impact of Gate Dielectric Material on Basic Parameters of MO(I)SHEMT Devices. ECS Meeting Abstracts, 2020, MA2020-01, 1373-1373.	0.0	0
186	Experimental silicon tunnel-FET device model applied to design a Gm-C filter. Semiconductor Science and Technology, 2020, 35, 095029.	2.0	0
187	Experimental Analysis of Trade-Off Between Transistor Efficiency and Unit Gain Frequency of Nanosheet NMOS Transistors. , 2021, , .		0
188	Analysis of the Negative-Bias-Temperature-Instability on Omega-Gate Silicon Nanowire SOI MOSFETs with Different Dimensions. Journal of Integrated Circuits and Systems, 2020, 15, 1-5.	0.4	0
189	Optimization of the Dual-Technology Back-Enhanced Field Effect Transistor. , 2020, , .		0
190	AlGaIn/GaN MISHEMT analysis from an analog point of view up to 150°C. , 2020, , .		0
191	Operational Transconductance Amplifier Designed with SiGe-source Nanowire Tunnel-FET using Experimental Lookup Table Model. , 2020, , .		0
192	Trade-off analysis between gm/ID and fT of nanosheet NMOS transistors with different metal gate stack at high temperature. Solid-State Electronics, 2022, 191, 108267.	1.4	0